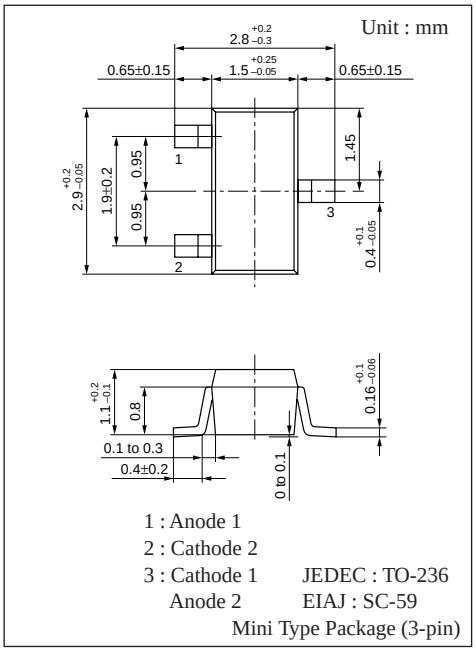
MA740

Silicon epitaxial planer type

For super high-speed switching circuit
For small current rectification

■ Features

- Two elements are incorporated in MA721 (series connection)
- Rectification with $I_{F(AV)}$= 200mA (single value)

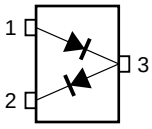


■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter		Symbol	Rating	Unit
Reverse voltage (DC)		V_R	30	V
Repetitive peak reverse voltage		V_{RRM}	30	V
Average forward current	Single	$I_{F(AV)}$	200	mA
	Double		130*1	
Peak forward current	Single	I_{FM}	300	mA
	Double		220*1	
Non-repetitive peak forward surge current	Single	I_{FSM}*2	1	A
	Double		0.7*1	
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	– 55 to +150	˚C

*1 Use value per chip
*2 50Hz sine wave, one-cycle wave, high value (non-repetitive)

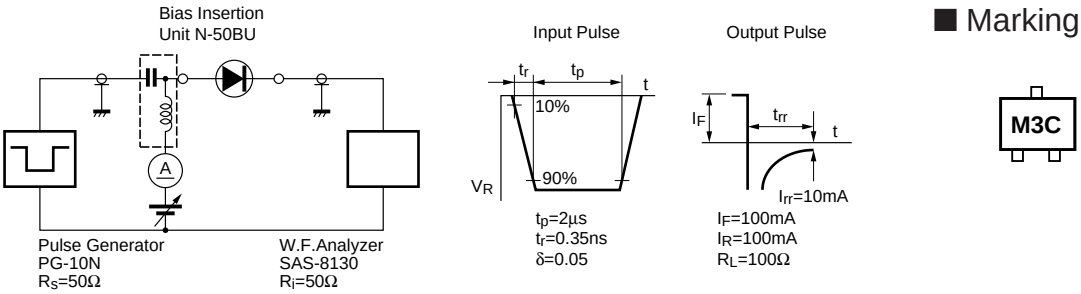
■ Internal Connection



■ Electrical Characteristics (Ta= 25˚C)

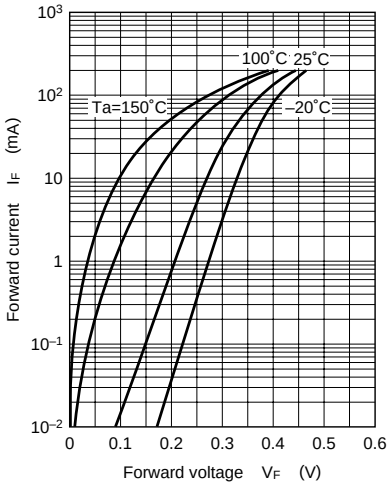
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R = 30V			50	µA
Forward voltage (DC)	V_F	I_F =200mA			0.55	V
Terminal capacitance	C_t	V_R = 0V, f=1MHz		30		pF
Reverse recovery time	t_{rr}*	I_F = I_R=100mA I_{rr}=10mA, R_L=100Ω		3		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 1000MHz
3. * t_{rr} measuring circuit

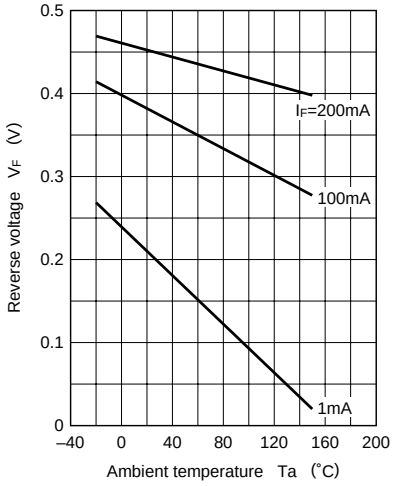


■ Marking

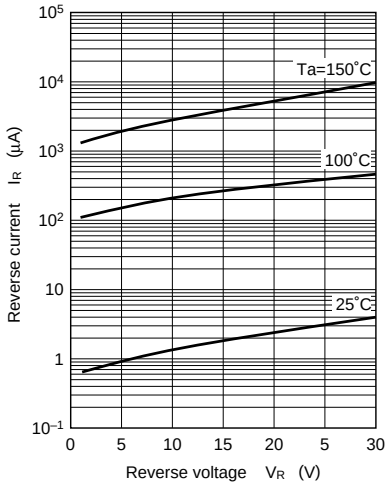
$I_F - V_F$



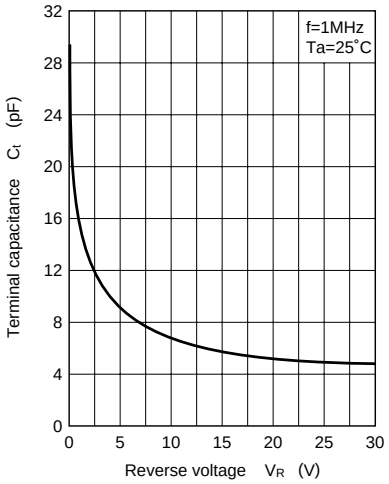
$V_F - Ta$



$I_R - V_R$



$C_t - V_R$



$I_R - Ta$